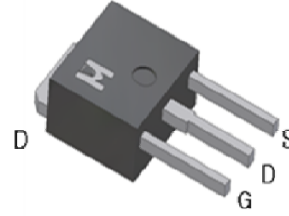


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	60V
$R_{DS(on)}$ (MAX.)	60m Ω
I_D	12A



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	I_D	12	A
	$T_C = 100\text{ }^\circ\text{C}$		8	
Pulsed Drain Current ¹		I_{DM}	30	
Avalanche Current		I_{AS}	12	
Avalanche Energy	$L = 0.1\text{mH}, I_D = 12\text{A}, R_G = 25\Omega$	E_{AS}	7.2	mJ
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	3.6	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	16.6	W
	$T_C = 100\text{ }^\circ\text{C}$		6.6	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		7.5	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		80	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS (T_c = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	2.0	3.2	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48V, V _{GS} = 0V			1	μA
		V _{DS} = 40V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	12			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 10A		50	60	mΩ
		V _{GS} = 5V, I _D = 8A		58	75	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 10A		19		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz		633		pF
Output Capacitance	C _{oss}			67		
Reverse Transfer Capacitance	C _{rss}			44		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		2.5		Ω
Total Gate Charge ^{1,2}	Q _g	V _{DS} = 20V, V _{GS} = 10V, I _D = 10A		13.8		nC
Gate-Source Charge ^{1,2}	Q _{gs}			2.8		
Gate-Drain Charge ^{1,2}	Q _{gd}			4.0		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = 20V, I _D = 1A, V _{GS} = 10V, R _{GS} = 6Ω		10		nS
Rise Time ^{1,2}	t _r			7.5		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			18		
Fall Time ^{1,2}	t _f			6		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_c = 25 °C)						
Continuous Current	I _S				12	A
Pulsed Current ³	I _{SM}				48	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.3	V
Reverse Recovery Time	t _{rr}	I _F = 5A, dI _F /dt = 100A / μS		15		nS
Reverse Recovery Charge	Q _{rr}				8	

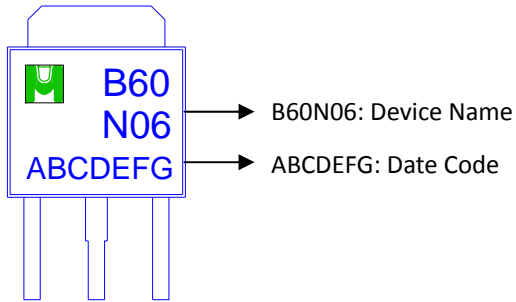
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

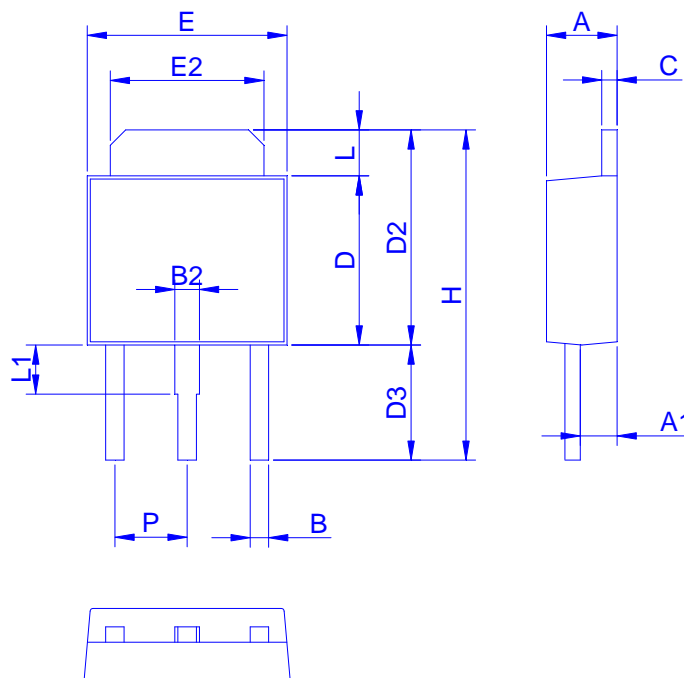
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB60N06C for IPAK (TO-251)



Outline Drawing



Dimension in mm

Dimension	A	A1	B	B2	C	D	D2	D3	E	E2	H	L	L1	P
Min.	2.18	0.89	0.63	0.76	0.46	5.97	6.86	3.2	6.35	4.95	10.06	0.89		
Nom.	2.29		0.76			6.10		3.3	6.60				1.05	2.29
Max.	2.39	1.14	0.85	1.05	0.61	6.22	7.49	3.4	6.73	5.46	10.89	1.27		



TYPICAL CHARACTERISTICS

